INCH-POUND MIL-M-38510/314C <u>14 July 2003</u> SUPERSEDING MIL-M-38510/314B 23 May 1978

MILITARY SPECIFICATION

MICROCIRCUITS, DIGITAL, LOW-POWER SCHOTTKY, TTL, MONOSTABLE MULTIVIBRATORS, MONOLITHIC SILICON

Inactive for new design after 18 April 1997.

This specification is approved for use by all Departments and Agencies of the Department of Defense.

1. SCOPE

1.1 <u>Scope.</u> This specification covers the detail requirements for monolithic silicon, low-power Schottky TTL, monostable multivibrator microcircuits. Two product assurance classes and a choice of case outlines and lead finishes are provided for each type and are reflected in the complete part number. For this product, the requirements of MIL-M-38510 have been superseded by MIL-PRF-38535, (see 6.3).

1.2 Part number. The part number should be in accordance with MIL-PRF-38535, and as specified herein.

1.2.1 <u>Device types.</u> The device types should be as follows:

Device type	<u>Circuit</u>
01	Dual monostable multivibrator, retriggerable, with clear
02	Dual monostable multivibrator, Schmitt trigger inputs, with clear
03	Single monostable multivibrator, retriggerable, with clear

1.2.2 Device class. The device class should be the product assurance level as defined in MIL-PRF-38535.

1.2.3 Case outlines. The case outlines should be as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	Terminals	Package style
А	GDFP5-F14 or CDFP6-F14	14	Flat pack
В	GDFP4-14	14	Flat pack
С	GDIP1-T14 or CDIP2-T14	14	Dual-in-line
D	GDFP1-F14 or CDFP2-F14	14	Flat pack
E	GDIP1-T16 or CDIP2-T16	16	Dual-in-line
F	GDFP2-F16 or CDFP3-F16	16	Flat pack
2	CQCC1-N20	20	Square leadless chip carrier

Beneficial comments (recommendations, additions, deletions) and any pertinent data which may be of use in improving this document should be addressed to: Commander, Defense Supply Center Columbus, ATTN: DSCC-VAS, P. O. Box 3990, Columbus, OH 43216-5000, by using the self addressed Standardization Document Improvement Proposal (DD Form 1426) appearing at the end of this document or by letter.

AMSC N/A <u>DISTRIBUTION STATEMENT A.</u> Approved for public release; distribution is unlimited.

FSC 5962

1.3 Absolute maximum ratings.

Supply voltage range Input voltage range	
Storage temperature range	65° to +150°C
Maximum power dissipation per flip-flop, (P _D) <u>1</u> /	
Device type 01	. 110 mW dc
Device type 02	
Device type 03	. 61 mW dc
Lead temperature (soldering, 10 seconds)	. 300°C
Thermal resistance, junction to case (θ_{JC}):	
Cases A, B, C, D, E, F, and 2	. (See MIL-STD-1835)
Junction temperature (T _J) <u>2</u> /	. 175°C

1.4 Recommended operating conditions.

Supply voltage (V _{CC})	4.5 V dc minimum to 5.5 V dc maximum
Minimum high level input voltage (V _{IH})	2.0 V dc
Maximum low level input voltage (VIL)	
Case operating temperature range (T _c)	-55° to +125°C
Minimum pulse width	
Input pulse rise/fall time, device type 02	
Schmitt, B input	1 V/s minimum
Logic, A input	
Clear-inactive-state setup time	·
Device type 02	15 ns minimum
External timing resistance, Rext	
Device type 01, 03	5 kΩ minimum, 180 kΩ maximum
Device type 02	
External timing capacitance, Cext	
Device type 01, 03	No restriction
Device type 02	1,000 μF maximum
Output duty cycle, device type 02	
$R_T = 2 k\Omega$	50% duty cycle maximum
T_T = 70 k Ω	90 % duty cycle maximum
Wiring capacitance, Rext/Cext terminal	
Device type 01, 03 (referenced to GND)	50 pF maximum

 <u>1</u>/ Must withstand the added P_D due to short-circuit test (e.g., I_{OS}).
 <u>2</u>/ Maximum junction temperature shall not be exceeded except for allowable short duration burn-in screening conditions in accordance with MIL-PRF-38535.

2. APPLICABLE DOCUMENTS

2.1 Government documents.

2.1.1 <u>Specifications and Standards</u>. The following specifications and standards form a part of this specification to the extent specified herein. Unless otherwise specified, the issues of these documents shall be those listed in the issue of the Departments of Defense Index of Specifications and Standards (DODISS) and supplement thereto, cited in the solicitation.

SPECIFICATION

DEPARTMENT OF DEFENSE

MIL-PRF-38535 - Integrated Circuits (Microcircuits) Manufacturing, General Specification for.

STANDARDS

DEPARTMENT OF DEFENSE

MIL-STD-883	-	Test Method Standard for Microelectronics.
MIL-STD-1835	-	Interface Standard Electronic Component Case Outlines

(Unless otherwise indicated, copies of the above specifications and standards are available from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.2 <u>Order of precedence.</u> In the event of a conflict between the text of this specification and the references cited herein, the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 <u>Qualification</u>. Microcircuits furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturers list before contract award (see 4.3 and 6.4).

3.2 <u>Item requirements</u>. The individual item requirements shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein.

3.3 <u>Design, construction, and physical dimensions.</u> The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein.

3.3.1 <u>Terminal connections and logic diagrams</u>. The terminal connections and logic diagrams shall be as specified on figure 1.

3.3.2 Truth table and functional description. The truth table and functional description shall be as specified on figure 2.

3.3.3 <u>Schematic circuits</u>. The schematic circuits shall be maintained by the manufacturer and made available to the qualifying activity and the preparing activity upon request.

3.3.4 Case outlines. The case outlines shall be as specified in 1.2.3.

3.4 Lead material and finish. The lead material and finish shall be in accordance with MIL-PRF-38535 (see 6.6).

3.5 <u>Electrical performance characteristics</u>. The electrical performance characteristics are as specified in table I, and apply over the full recommended case operating temperature range, unless otherwise specified.

3.6 <u>Electrical test requirements.</u> The electrical test requirements for each device class shall be the subgroups specified in table II. The electrical tests for each subgroup are described in table III.

3.7 Marking. Marking shall be in accordance with MIL-PRF-38535.

3.8 <u>Microcircuit group assignment</u>. The devices covered by this specification shall be in microcircuit group number 10 (see MIL-PRF-38535, appendix A).

4. VERIFICATION

4.1 <u>Sampling and inspection</u>. Sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not effect the form, fit, or function as described herein.

4.2 <u>Screening</u>. Screening shall be in accordance with, MIL-PRF-38535 and shall be conducted on all devices prior to qualification and quality conformance inspection. The following additional criteria shall apply:

- a. The burn-in test duration, test condition, and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document control by the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015 of MIL-STD-883.
- b. Interim and final electrical test parameters shall be as specified in table II, except interim electrical parameters test prior to burn-in is optional at the discretion of the manufacturer.
- c. Additional screening for space level product shall be as specified in MIL-PRF-38535, appendix B.

4.3 <u>Qualification inspection</u>. Qualification inspection shall be in accordance with MIL-PRF-38535.

4.4 <u>Technology Conformance Inspection (TCI)</u>. Technology conformance inspection shall be in accordance with MIL-PRF-38535 and herein for groups A, B, C, and D inspections (see 4.4.1 through 4.4.4).

4.4.1 Group A inspection. Group A inspection shall be in accordance with table III of MIL-PRF-38535 and as follows:

- a. Tests shall be as specified in table II herein.
- b. Subgroups 4, 5, and 6 shall be omitted.

TABLE I. Electrical performance characteristics.

Test	Symbol	Conditions	Device	Lin	nits	Unit
		$-55^{\circ}C \le T_{C} \le +125^{\circ}C$	types	Min	Max	
		unless otherwise specified				
High level output voltage	V _{он}	$V_{CC} = 4.5 \text{ V}, \text{ V}_{IL} = 0.7 \text{ V},$	All	2.5		V
		$V_{IH} = 2.0 \text{ V}, I_{OH} = -400 \mu\text{A}$				
Low level output voltage	Vol	$V_{CC} = 4.5 \text{ V}, \text{ V}_{IL} = 0.7 \text{ V},$	All		0.4	V
		$V_{IH} = 2.0 \text{ V}, I_{OL} = 4 \text{ mA}$				
Input clamp voltage	V _{IC}	$V_{CC} = 4.5 \text{ V}, \text{ I}_{IN} = -18 \text{ mA},$	All		-1.5	V
		T _C = +25°C				
Low level input current	I _{IL1}	$V_{CC} = 5.5 \text{ V}, \text{ V}_{IN} = 0.4 \text{ V}$	01, 03	-160	-400	μA
Low level input current	I _{IL2}		02	-30	-680	
at clear input						
Low level input current at A_{IN}			02	-30	-400	
Low level input current BIN	-		02	-30	-580	
High level input current	I _{IH1}	$V_{CC} = 5.5 \text{ V}, \text{ V}_{IN} = 2.7 \text{ V}$	All		20	μA
High level input current	I _{IH2}	$V_{CC} = 5.5 \text{ V}, \text{ V}_{IN} = 5.5 \text{ V}$	All		100	
Short circuit output current	I _{OS}	$V_{CC} = 5.5 \text{ V}, \text{ V}_{IH} = 5.5 \text{ V},$	All	-15	-130	mA
		V _{IL} = GND				
Supply current (quiescent)	I _{CC1}	$V_{CC} = 5.5 V$	02		11	mA
Supply current (quiescent or	I _{CC2}	-	01		20	
triggered)	-002		03		11	
Supply current (triggered)	I _{CC3}		02		27	
Propagation delay time low to	t _{PLH1}	V _{CC} = 5.0 V	01, 03	5	57	ns
high level from input A		C_L = 50 pF ±5%, R_L = 2 k Ω ±5%	02	5	113	
Propagation delay time low to	t _{PLH2}	Cext = <u>1</u> /	01, 03	5	74	
high level from input B		Rext = <u>1</u> /	02	5	90	
Propagation delay time low to	t _{PLH3}		01, 03	5	75	
high level from clear			02	5	105	
Propagation delay time	t _{PHL1}		01, 03	5	75	
high to low level from input A			02	5	128	

See footnotes at end of table.

Test	Symbol	Conditions	Device	Lin	nits	Unit
		$-55^{\circ}C \le T_{C} \le +125^{\circ}C$	types	Min	Max	
		unless otherwise specified				
Propagation delay time	t _{PHL2}	$V_{CC} = 5.0 V$	01, 03	5	92	ns
high to low level from input B		$C_{L} = 50 \text{ pF} \pm 10\%$	02	5	105	
		$R_L = 2k\Omega \pm 5\%$				
Propagation delay time	t _{PHL3}	Cext = <u>1</u> /	01, 03	5	48	ns
high to low level from clear		Rext = <u>1</u> /	02	5	90	
Minimum pulse width	t _{P(MIN)}	$V_{CC} = 5.0 V$	01, 03		308	ns
of Q output		$C_L = 50 \text{ pF} \pm 10\%$				
Width of Q output pulse	t _{P1}	$R_L = 2k\Omega \pm 5\%$	02	20	91	
	t _{P2}	Cext = <u>2</u> / ±10%	02	70	195	
	t _{P3}	Rext = <u>2</u> / ±10%	02	600	850	
	t _{P4}		01, 03	3.0	6.25	μs
	t _{P5}		02	5.5	8.5	ms

TABLE I. Electrical performance characteristics - Continued.

1/ For propagation delay tests, see table III for Cext and Rext values.

<u>2</u>/ $t_{P(MIN)}$ test, Cext = open and Rext = 5 k Ω .

 t_{P1} test, Cext = open and Rext = 2 k Ω .

 t_{P2} test, Cext = 80 pF and Rext = 2 k Ω .

 t_{P3} test, Cext = 100 pF and Rext = 10 k $\Omega.$

 t_{P4} test, Cext = 1,000 pF and Rext = 10 k Ω .

 t_{P5} test, Cext = 1µF and Rext = 10 kΩ.

	Subgroups	(see table III)
MIL-PRF-38535	Class S	Class B
test requirements	devices	devices
Interim electrical parameters	1	1
Final electrical test parameters	1*, 2, 3, 7, 9, 10, 11	1*, 2, 3, 7, 9
Group A test requirements	1, 2, 3, 7, 8, 9, 10, 11	1, 2, 3, 7, 8, 9
Group B electrical test parameters	1, 2, 3	N/A
when using method 5005 QCI option	9, 10, 11	
Group C end-point electrical parameters	1, 2, 3,	1, 2, 3
	9, 10, 11	
Additional electrical subgroups for	N/A	10, 11
group C inspections		
Group D end-point electrical parameters	1, 2, 3	1, 2, 3

TABLE II. Electrical test requirements.

*PDA applies to subgroup 1.

4.4.2 Group B inspection. Group B inspection shall be in accordance with table II MIL-PRF-38535.

4.4.3 Group C inspection. Group C inspection shall be in accordance with table IV of MIL-PRF-38535 and as follows:

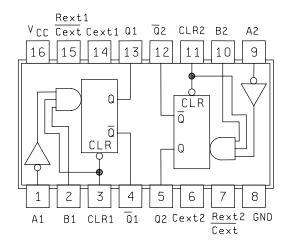
- a. End-point electrical parameters shall be as specified in table II herein.
- b. The steady-state life test duration, test condition, and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document control by the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.
- c. Subgroups 3 and 4 shall be added to group C inspection parameters for class B devices and shall consist of the tests, conditions, and limits specified for subgroups 10 and 11 of group A.

4.4.4 <u>Group D inspection</u>. Group D inspection shall be in accordance with table V of MIL-PRF-38535. End-point electrical parameters shall be as specified in table II herein.

4.5 <u>Methods of inspection</u>. Methods of inspection shall be specified and as follows:

4.5.1 <u>Voltage and current.</u> All voltages given are referenced to the microcircuit ground terminal. Currents given are conventional and positive when flowing into the referenced terminal.

DEVICE TYPE 01 CASES E AND F



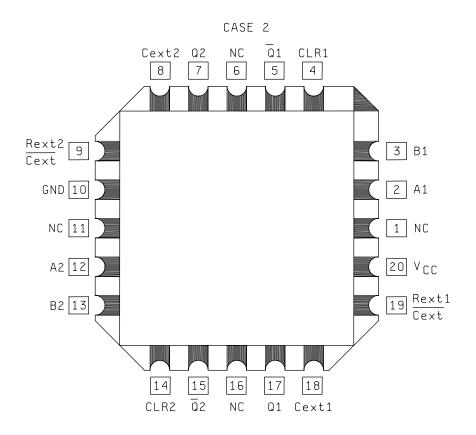
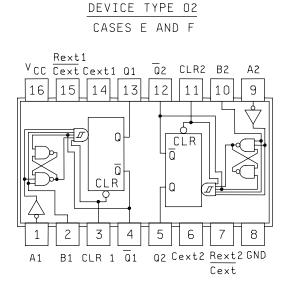


FIGURE 1. Terminal connections.



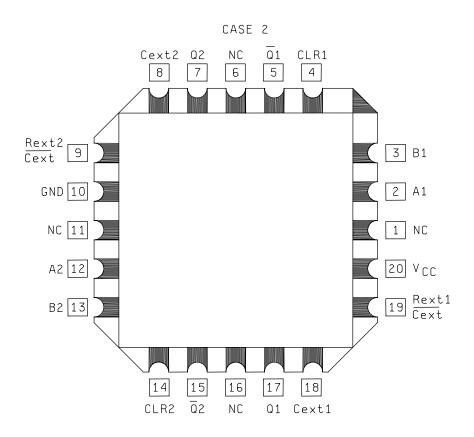
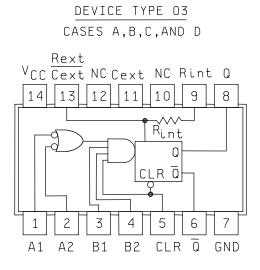


FIGURE 1. Terminal connections - Continued.



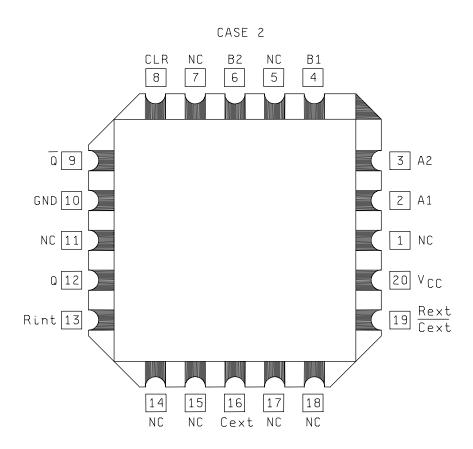


FIGURE 1. Terminal connections - Continued.

Device type 01 and 02

I	NPUTS		OUT	PUTS
CLEAR	А	В	Q	IQ
L	Х	Х	L	Н
Х	н	Х	L	Н
Х	Х	L	L	Н
н	L	\uparrow		Ц
Н	\downarrow	Н		Ц
↑	L	Н		Ц

Device type 03

		INPUTS			OUT	PUTS
CLEAR	A1	A2	B1	B2	Q	IQ
L	Х	Х	Х	Х	L	Н
Х	Н	Н	L	Н		
Х	Х	Х	L	Х	L	Н
Х	Х	Х	Х	L	L	Н
Н	L	Х	\uparrow	Н	Г	IJ
Н	L	Х	Γ			
Н	Х	L	\uparrow	Н	П	Ц
Н	Х	L	Н	\uparrow	П	Ц
н	Н	\downarrow	Н	Н	Г	
Н	\downarrow	\downarrow	Н	Н	Γ	Ц
Н	\downarrow	Н	Н	Н	Г	
\uparrow	L	Х	Н	Н	Γ	IJ
\uparrow	Х	L	Г	Ц		

NOTES:

1. H = high level (steady state), L = low level (steady state), ↑ = transition from low to high level,

 \downarrow = transition from high to low level, \square = one high level pulse, \square = one low level pulse,

X = irrelevant (any input, including transitions).

2. To use the internal timing resistor of device type 03 connect Rint to V_{CC} .

3. An external timing capacitor may be connected between Cext and Rext/Cext (positive).

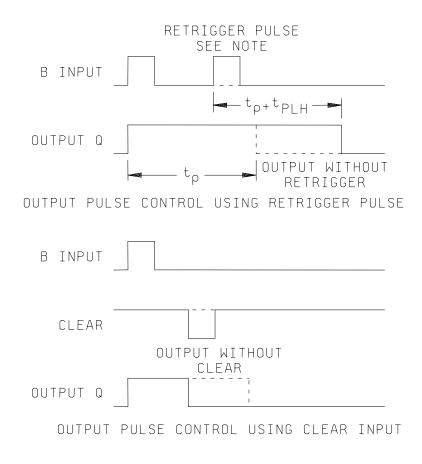
4. For accurate repeatable pulse widths, connect an external resistor between Rext/Cext and V_{CC} with Rint open circuited.

5. To obtain variable pulse widths, connect external variable resistance between Rint or Rext/Cext and V_{CC}.

FIGURE 2. Truth table and functional description.

Device types 01 and 03

This multivibrator features d-c triggering from gated low level active (A inputs), and high level active (B inputs). Output pulse width is a function of external capacitor and resistor values. Retriggering of input before output terminates, extends output pulse width. Overriding clear feature permits termination of output pulse width at a predetermined time independent of R and C timing components.



NOTE:

Retrigger pulse must not start before 0.22 Cext (in picofarads) nanoseconds after previous trigger pulse.

FIGURE 2. Truth table and functional description - Continued.

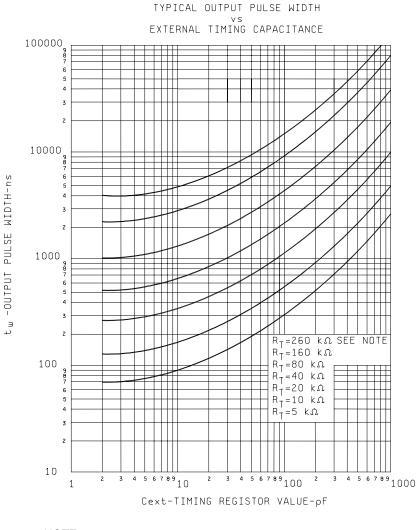
Device type 01 and 03 (Continued)

The output pulse width (tp) is a function of the external capacitor and resistor values.

For output pulse widths when Cext > 1,000 pF, tp is defined as :

tp $\approx 0.4 R_T Cext$ Where R_T is in k Ω , Cext is in pF, and tp is in ns.

For output pulse widths when Cext < 1,000 pF, tp is defined as:



NOTE:

This value of resistance exceeds the maximum recommended for use over the full temperature range

FIGURE 2. Truth table and functional description - Continued.

Device type 02

This multivibrator features a negative transition triggered input and a positive transition triggered input, either of which can be used as an inhibit input. Pulse triggering occurs at a particular voltage level, not directly related to transition time of input pulse. Once fired, the outputs are independent of further transitions of A and B inputs, and are a function of the timing components. Output pulses can be terminated by the overriding clear, independent of R and C timing components.

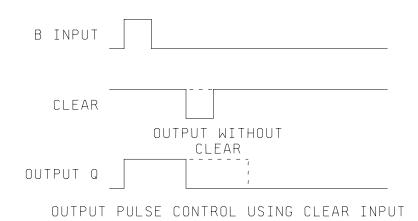


FIGURE 2. Truth table and functional description - Continued.

Device type 02 (Continued)

The output pulse width (tp) is a function of the external capacitor and resistor values.

The output pulse width is defined as :

tp $\,\approx\,$ 0.7 R_T Cext $\,$ Where R_T is in k\Omega, Cext is in pF, and tp is in ns.

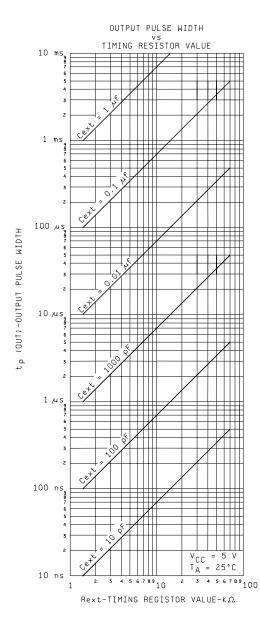
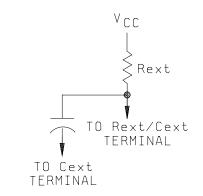


FIGURE 2. Truth table and functional description - Continued.

DEVICE TYPES 01,02 AND 03



TIMING COMPONENT CONNECTIONS

FIGURE 2. Truth table and functional description - Continued.

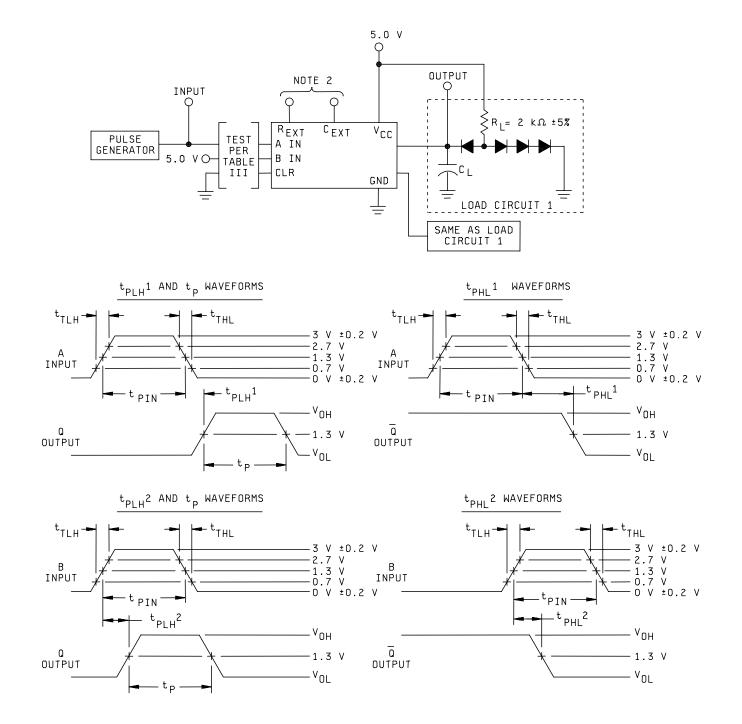
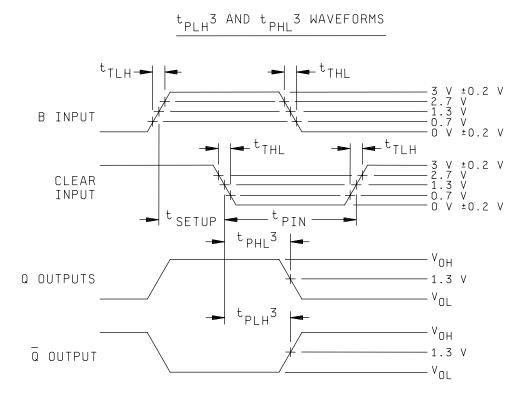


FIGURE 3. Switching test circuit and waveforms for device types 01 and 03.



NOTES:

- 1. Pulse generator has the following characteristics: PRR \leq 1.0 MHz, t_{PIN} \geq 40 ns, t_{THL} \leq 6 ns, t_{TLH} \leq 15 ns, and Z_{OUT} = 50 Ω .
- 2. See table III notes for Rext, Cext values.
- 3. $C_L = 50 \text{ pF} \pm 10\%$ including scope probe, wiring and stray capacitance, without package in test fixture.
- 4. All diodes are 1N3064, or 1N916 or equivalent.
- 5. Load circuit on a given output is only required where the specified test in table III indicates "OUT" on that output.
- 6. t_{SETUP} (max) shall be \leq 50% of the typical output pulse width for the actual Cext used (see figure 2).

FIGURE 3. Switching test circuit and waveforms for device types 01 and 03 - Continued.



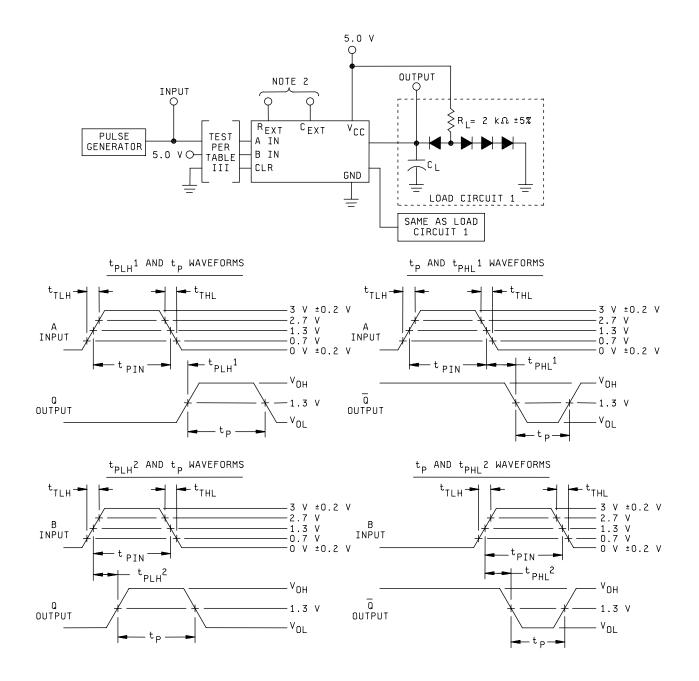
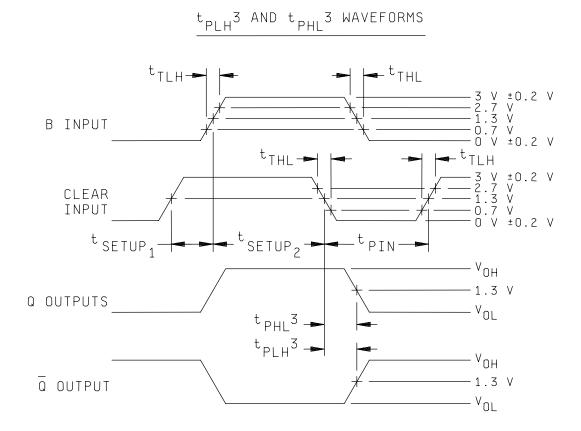


FIGURE 4. Switching test circuit and waveforms for device type 02.



NOTES:

- 1. Pulse generator has the following characteristics: PRR \leq 1.0 MHz, t_{PIN} \geq 40 ns, t_{TLL} \leq 6 ns, t_{TLH} \leq 15 ns, t_{SETUP1} (CLEAR INACTIVE) = 15 ns and Z_{OUT} = 50 Ω .
- 2. See table III notes for Rext, Cext values.
- 3. $C_{L} = 50 \text{ pF} \pm 10\%$ including scope probe, wiring and stray capacitance, without package in test fixture.
- 4. All diodes are 1N3064, or 1N916 or equivalent.
- 5. Load circuit on a given output is only required where the specified test in table III indicates "OUT" on that output.
- 6. t_{SETUP} (max) shall be \leq 50% of the typical output pulse width for the actual Cext used (see figure 2).

FIGURE 4. Switching test circuit and waveforms for device type 02 - Continued.

	Unit		>	=			=	=	-	=	=	-	=	-		V.	5	-	-	-	=	-		=	-		=	-				шA	-	=	=	=		-	-	=
	lits	Max					0.4	-	=	-	-1.5	-	-			-400	=	-	=	-	=	20		-	-		100	-				-100	-130	-100	-130	001	-100	-130	-100	-130
	Limits	Min	2.5	=	=	-										-160	=	=	=	-	=											-15	-30	-15	-30	15	GL-	-30	-15	-30
	Measured terminal		ā1	Q1	_ Q2	Q2	Q1	a' 19	Q2	ō2	A1	B1	CLR1	A2	B2 CLDC	ULKZ A1	14 14	CLR1	A2	B2	CLR2	A1	B1	ULK1 A2	B2	CLR2	A1	B1	CLR1	A2 50	BZ CLR2	ā1	a1	a1	α1	1	ā2	ā2	Q2	Q2
16	20	V _{cc}	4.5 V	-	=	-	=	-	-	-	-	-	-			55V	> ? ?	-	-	-	=	-		-	-	-	-	-				-	-	-	=	-		-	=	-
15	19	Rext1		GND				GND																										GND	GND					
14	18	Cext1																																		T				
12 13 1	17	ø		4 mA			4 mA																											GND	GND	T				
12	15	ā2			4 mA					4 mA																											GND	GND		
11	14	CLR2			2.0 V	2.0 V			2.0 V	2.0 V					V 07	-18 mA					0.4 V					2.7 V					55V						GND	GND	4.5 V	4.5 V
10	13	B2			0.7 V	2.0 V			0.7 V	2.0 V					-18 mA					0.4 V					2.7 V					2	V C.C						GND	GND	4.5 V	4.5 V
5 6 7 8 9 10	12	A2			2.0 V	с U			2.0 V	υ				-18 mA	T	T		Ī	0.4 V					271	i				1	5.5 V							GND	GND	ы	с
ω	10	GND	GND	-	-	-	=	-	-	-	-	-	-			-	-	-	-	-	-	-		-	-	-	-	-					-	-	-	-		-	-	-
2	თ	Rext2				GND				GND																													GND	GND
9	ω	Cext2													T	T		ľ		l																T				
S	7	Q2				4 mA			4 mA						T	T		Ī		Ī																1			GND	GND
4	2	ā1	4 mA					4 mA							T	T		Ī		Ī												GND	GND			T				
e	4	CLR1	2.0 V -	2.0 V			2.0 V						-18 mA		T			0.4 V						Z. / V					5.5 V			GND	GND	4.5 V	4.5 V	+				
2	ю		0.7 V	2.0 V			0.7 V					-18 mA	•		T		0.4.V	+					2.7 V					5.5 V				GND	GND	4.5 V	4.5 V	+				
1	5		2.0 V	С			2.0 V				-18 mA	'			T	041		+				2.7 V		+			5.5 V				+	GND	GND	υ	с 0	╉				
Cases E, F	Case 2	Test no.	.	2	e	4			7	80		10	11	12	13	15 (17	18	19	20	_	22	23 24	25			28	29	30	37	33 CKT 0		34 CKT	34 CKT	C C	A, D	35 CKT C	36 CKT A. D	36 CKT
-MIL-	STD-883 method -	1	3006	=		-	3007	-	-	-		<u> </u>	<u> </u>			3009	8	-	-	-	1	0		=	-	-	=	-				3011	-	-	-			-	-	-
	Symbol S		V _{он}				VoL				Vic					,	Soo Soo	note K				I _{H1}					I _{H2}					los								
	Subgroup S		٢	Γc = 25°C			1				1					_1_		_	_								I					1								

TABLE III. Group A inspection for device type 01.

		Unit		mA	шA																				ns	-	-		-	=	-	=	-	=	-		=	-	-	-
		ts	Max	20	20			See notes	Å, B, D,	E and F					-	-	-	-	-	=	=	-	-	ĺ	38	38	49	49	50	-	-	-	61	61	32	32	205	-	-	
		Limits	Min																						5	=	-	-	-	-	-	-	-	-	-	-				
		Measured terminal		Vcc	V _{cc}			AII	outputs					-	-	-	=	-	-	-		-	-		A1 to Q1	A2 to Q2	B2 to Q2	B1 to Q1	CLR1 to Q1	CLR2 to Q2	A2 to G2	A1 to G1	B1 to 01	B2 to 02	CLR2 to Q2	CLR1 to Q1	a1	Q1	Q2	Q2
	16	20	V _{cc}	5.5 V	5.5 V		-	5.0 V							-	-	-	-		-			-		5.0 V	-	-	-	=	=	-	-	=	-	-	-	=	-	-	-
	15	19	Rext1				ſ	ш							=	-	=	-		=			-		ш			ш	_			ш	ш]	IJ	U		
1/	14	18	Cext1 F				-	ш							_	_	-	=		-	-	-	-		ш			ш				ш	ц			1	Open	Open	_	
open).	13						-			_	т.			-				г																		Л				
, V, or 6	1	17	ø				-	_		-	± .		-	E		-	-	-		=	-	-	=		OUT			OUT								OUT	OUT	OUT		
w ≤ 0.7	12	15	02 Q2				_	Т	-	•		I	•	-	T	-	=	_	Т	-	-	-	-							OUT	OUT			OUT						
0 V, lo	11	14	CLR2	5.5 V	5.5 V			в	-		4 ا	ш	л -	A 4	< m	ш	A	A	В	A	-	=	-			5.0 V	5.0 V			Z	5.0 V			5.0 V	≥				5.0 V	5.0 V
Terminal conditions (pins not designated may be high ≥ 2.0 V, low ≤ 0.7 V, or open)	10	13	B2	5.5 V	5.5 V			A	B	A :		- 1	<u></u>	ס⊲	: =	-	=	-	В	в	A	В	в			5.0 V	Z			Z	5.0 V			Z	≥				5.0 V	Z
lay be l	6	12	A2	5.5 V	υ		-	A	A	en •					-	A	A	ш	В	A	-		в			Z	GND			GND	≥			GND	GND				z	GND
nated m	ω	10	GND	GND	GND	ed.		GND							-	=	=	=		-	-	-	-	ĺ	GND	=	-	-	-	-	-	-	-	-	-	-	=	=	-	
t design	7	ი	Rext2			are omitt	ire omitted	ш							-	-	-	-		-	-	-	-			ш	ш			_	ш			ш	_				ი	U
pins no	9	œ	Cext2			I V _{IC} tests	/ _{IC} tests a	ш							=	=	-	=		=			-			ш	ш]	ш			ш	_				OPEN	DPEN
litions (ى ع	7	Q2 (125°C and	5°C and \	-		. :	т.			- 1	:	=	=	г	L	-	-	-	-			OUT	DUT								DUT				0UT 0	
ial conc	4	5	a'			spt T _c = +'	spt T _C = -5	н			_:	I.			ı I	=	=	_	н	-	-	-	-			_	-		OUT			OUT	OUT						_	_
Termir	e	4	CLR1	5.5 V	5 V	up 1, exce	up 1, exc∈	в			A	<u>а</u>	а -	A	. 8	в	A	A	В	A	-	-	-		5.0 V			>	N N				5.0 V C			z	5.0 V	0 \	_	_
	2	e	B1 CI	5.5 V 5.	5 V 5.	or subgro	or subgro	A	m	A :			<u></u>	ס ⊲		_	=	_	В	m	A	В	m		5.0 V 5.			IN 5.				>	IN 5.				5.0 V 5.		_	_
					5.6	imits as fo	imits as fo	_			_										'			1d T _c = -5												_				_
	se .	e 5	10. A1	5.5 V	0	ons, and i	ons, and	4	A				-		-	A		B	В	A	-	-	В	+125°C	Z		_		GND				GND			GND			┥	-
	Cases E, F	3 Case	Test no.	37	38	<u>al conditi</u>	nal conditi	39	40	41	42	43	44	45	47	48	49	50	51	52	53	54	55		56	57	58	59	60	61	62	63	64	65	99	67	68	69	20	71
	-MIL-	STD-883 method -		3005	3005	Same tests, terminal ∞ nditions, and limits as for subgroup 1, except T $_{ m C}$ = +125°C and V $_{ m C}$ tests are omitted.	Same tests, terminal conditions, and limits as for subgroup 1, except T_c = -55°C and V_{lc} tests are omitted	3014							-	-	-	-	-	-	-	-	-	Repeat subgroup 7	3003	Fig. 3	-	-	-	-	-	-	=	-	-	•	=	-		-
		Symbol		I _{CC2}		Same te	Same te			tests														Repeat :	tPLH1		t _{PLH2}		t _{PLH3}		t _{PHL1}		t _{PHL2}		t _{PHL3}		t _{P(MIN)}			
		Subgroup Symbol		-	Tc = 25°C	2	3	7	Tc = 25°C					_										8	6	$Tc = 25^{\circ}C$		_												

TABLE III. Group A inspection for device type 01.

See footnotes at end of this table.

		Unit		sn	=					
		ts	Max	6.0	=	-	-			
		Limits	Min	3.5	-	-	=			
		Measured terminal		Q2	Q2	α1	α1			
	16	20	V _{cc}	5.0 V						
	15	19	Rext1			_	_			
.). <u>1</u> /	14	18	Cext1			_	_	to 75 ns;		
or oper	13	17	ø			OUT	OUT	t _{PLH3} is 5		
<u>1</u> . ≤ 0.7 V,	12	15	_ Q2					to 74 ns;		
TABLE III. Group A inspection for device type 01. Terminal conditions (pins not designated may be high ≥ 2.0 V, low ≤ 0.7 V, or open). 1/		14	CLR2	5.0 V	5.0 V			t _{PLH2} is 5		
for devic iigh ≥ 2.0	10	13	B2	Z	5.0 V			to 57 ns;		
pection lay be h	ი	12	A2	GND	Z			t _{PLH1} is 5		
ip A inst nated m	œ	10	GND	GND		-	=	follows:	.25 μs.	
II. Grou	7	თ	Rext2	_	_			ts are as	s 3.0 to 6	
FABLE I (pins n	9	ω	Cext2	_	-			and limi	and t _{P4} i	°C
T Inditions	5	7	Q2	DUT	DUT			= +125°C	s 308 ns;	: T _c = -55°C
minal cc	4	5	°10					cept T _c =	s; t _{P(MIN)} i	0, except
Terr	e	4	CLR1			5.0 V	5.0 V	oup 9, ex	5 to 48 n:	bgroup 1
	2	e	B1			5.0 V	N	as subgr	; t _{PHL3} is ;	as for su
	-	2	A1			Z	GND	nditions	to 92 ns	nditions
	Cases E, F	Case 2	Test no.	72	73	74	75	srminal cc	; t _{PHL2} is 5	rminal cc
	MIL-	Subgroup Symbol STD-883 method -	•	3003	Fig. 3	-		Same tests and terminal conditions as subgroup 9, except T _c = +125°C and limits are as follows: t _{bLH} is 5 to 77 ns; t _{bLH2} is 5 to 74 ns; t _{bLH3} is 5 to 77 ns;	t_{PHL1} is 5 to 75 ns; t_{PHL2} is 5 to 92 ns; t_{PHL3} is 5 to 48 ns; $t_{P(MN)}$ is 308 ns; and t_{P4} is 3.0 to 6.25 μ s.	¹¹ Same tests and terminal conditions as for subgroup 10, except 1
		Symbol		t _{P4}				Same te	t _{PHL1} is:	Same te
		Subgroup		ი	Tc = 25°C			10		11

NOTES:

- A. $V_{IN} = 3.0 V$ minimum.
- B. $V_{IN} = 0.0 V$ or GND.
- C. Apply input pulse

_______ - - - - 2.5 V min/5.5 V max. 0 V

D. Test numbers 39 through 55 shall be run in sequence.

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E. Output voltages shall be either:

H > 1.5 V; L < 1.5 V

- F. Rext = 5 kΩ minimum to 180 kΩ maximum, connected to V_{cc} ; Cext ≤ 1,000 µF, connected to Rext terminal.
- G. Rext = 5 k $\Omega \pm 10\%$, connected to V_{cc}.
- 1. Rext = 10 kΩ \pm 10%, connect to V_{cc}; Cext \leq 1,000 μF \pm 10%, connected to Rext terminal.
- J. During subgroups 9, 10, 11 testing, Rext and Cext may remain applied on the side of the device not under test if desired.
- K. For circuit D, $I_{\rm Ic1}$ limits are 120 mA to 360 mA.
- L. Rext = 10 k\Omega \pm 10%, connect to V_{cc}; Cext \ge 45 pF connected to Rext terminal.

		Unit		>	-	=	=	-	-	=	-	-	-	-	=			۲'n	=	-	-	-	-	-	-	=	=	-	-	-	-	-	-	-	-	-	=	=				-	-	-
		ts	Max					0.4	-	-	=	-1.5	-		-			-340	-300	-400	-580	-300	-440	-680	-300	-340	-300	-400	-580	-300	-440	-680	-300	20	=	-	-	=	= 0	100				-
		Limits	Min	2.5	-	-	=										001	-100	-30	-160	-160	-30	-200	-200	-30	-100	-30	-160	-160	-30	-200	-200	-30											
		Measured terminal		۱۵	۵1 م	02 02	Q2	۵1 م	٩	Q2	- Q2	A1	B1	CLR1	A2	B2	CLR2	A1	A1	A1	B1	B1	B1	CLR1	CLR1	A2	A2	A2	B2	B2	B2	CLR2	CLR2	A1	B1	CLR1	A2	B2	CLR2	A1 - :	B1		AZ B2	CLR2
	16	20	V _{cc}	4.5 V	-	-	-		-	=	-	-	-	-	-			A د.د	-		-	-		-	-	=	-	-	-	-	-	-	-	-	-	-	-	-					-	-
	15	19	Rext1 See L		GND			-	GND															GND	GND																T			
	14		Cext1 See L		GND				GND															GND	GND				-						┢				+	+				
or open	13		a1 s		4 mA			4 mA																		, 													+	+	╉	+		
, low ≤ 0.7 V, or open).	12	15	ā2		7 ⁻ -	4 mA		4			4 mA																												+	+	╉	+	+	
/, Iow ≤							>									4	hA									>						0			F	H		Δ	>	_	+			>
i ≥ 2.0 V,	1	14	CLR2			/ 2.0 V	/ 2.0 V				/ 2.0 V						-18 mA									/ 4.5 V	-	-		=	-	dnD	/ GND		╞	H		GND		_	+	_	+	5.5 V
designated may be high	10	13	B2			0.7 V	2.0 V			0.7 V	2.0 V					-18 mA										4.5 V	-		0.4 V	=	-	4.5 V	4.5 V		L			2.7 V	_				_	GND
d may	თ	12	A2			2.0 V	ပ			2.0 V	U U				-18 mA											0.4 V	-	-	GND	-	-	-	-		L		2.7 V	4.5 V	4.5 V	_	_	55/	5.5 V	4.5 V
signate	ø			GND	-	-	-	-	-	=	-	-	-	-	-		-		-	-	-	=	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	=				-	-	-
s not de	7	6	Rext2 See L				GND				GND																					GND	GND											
ditions (pins not designated may be high \geq	9	œ	Cext2 See L				GND				GND																					GND	GND											
conditio	5	7	Q2				4 mA			4 mA																																		
Terminal con	4	5	ā1	4 mA					4 mA																																			
Те	3	4	CLR1	2.0 V	2.0 V			2.0 V	2.0 V					-18 mA			1 5 11	4.5 V	-	-	-	=	-	GND	GND										GND	2.7 V				<u>(</u>	GND	2.0 V		
	7	с	B1	0.7 V	2.0 V			0.7 V	2.0 V				-18 mA				1 5 1	4.5 V	=	-	0.4 V	-	-	4.5 V	4.5 V										2.7 V	GND					5.5 V	פואה		
	-	5	A1	2.0 V	υ			2.0 V	υ			-18 mA					~ * * 0	0.4 V	-		GND	=	-	-	-		l							2.7 V	4.5 V	4.5 V				5.5 V	4.5 V	V C.4		
	Cases E, F	Case 2	Test no.	-	2	e	4	5	9	7	8	- 6	10	11	12	13	14 5 CI/T	A, C, D	5 CKT B	5 CKT E	16 CKT A. C) CKT B	16CKT E. D		CKTB	18 CKT A. C. D	CKT B	3 CKT E	9 CKT A. C) CKT B	19 CKT F D	20 CKT A C D F	CKTB				24	25			28	20	31	32
		STD-883 method -	F	3006	-	-	-	3007	-	-	-							1 6005			-		-	- 4 -	=		16	" 18	-	16	-	-	- 20	3010	-		-	-						_
	2			V _{он} 3				VoL 3				Vic					_	3																IH1 3					+	H2				
		Subgroup Symbol		7	25°C			>				>						_																					<u> </u>	-				_
		Subg			Tc = 25°C																																							

TABLE III. Group A inspection for device type 02.

See footnotes at end of this table.

		Unit		ШA	-	=	-	-	=	-	-	=	=				~	dΕ																		
		its	Max	-100	-130	-100	-130	-100	-130	-100	-130	11	27				See notes	A, B, D, E, and F																		
		Limits	Min	-15	-30	-15	-30	-15	-30	-15	-30							À, E																		
		Measured terminal		Q1	۵1 م	_ Q2	_ 02	Q2	Q2	ō,	٩. م	Vcc	Vcc			AII	outputs	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	=	-	-	
	16	20	V _{cc}	5.5 V		-	-	-	-	-	-	-	=			5.0 V	=	-	-	-	-	-	-	-	-	-	-	-	=	=	-	-	-	-	-	
	15	19	Rext1 See L	GND	GND											ш	=	=	=	-	=	=	=	-	=	-	-	-	-	=			-	=	-	
n).	14	18	Cext1 See L	GND	GND											ш	-	-	-	-	-	-	-	-	-	-	-	-	-	=		-		-	-	
, or ope	13	17	ø	GND	GND							Ì					-	-	н	_	-	-	т	_	-	-	т	_	-	=	=	=	=	-	-	
Terminal conditions (pins not designated may be high ≥ 2.0 V, low ≤ 0.7 V, or open)	12	15	ā2			GND	GND									т	=	=	L	т	=		L	т	=	-		=	=	L	н			-	-	
0 V, Iow	11	14	CLR2			GND	GND	4.5 V	4.5 V			5.5 V	5.5 V			в	=	-	A	В	в	A	A	в	-	-	-	-	A	A	В	A	=	-	-	
nigh ≥ 2.	10	13	B2			GND	GND	4.5 V	4.5 V			GND	5.5 V			A	в	A	-	-	в	в	A	-	-	-	-	-	-	=	В	В	A	В	В	
nay be l	6	12	A2			GND	GND	с U	ပ			5.5 V	c			A	A	в	-	-	-	-	-	-	A	-		=	=	в	В	A		-	В	
jnated r	8	10	GND	GND		=	=	-	-	-	=	=	-	ed.		GND	-	-	-	-	-	-	-	-	-	-		-	-	=		-		-	-	
not desig	7	ი	Rext2 See L					GND	GND					are omitte	55°C and V _{IC} tests are omitted.	ш	-	-	-		-	=	=		-			-	-	=		=	-	-	-	
s (pins r	9	œ	Cext2 See L					GND	GND			Ì		d V _{IC} tests	V _{IC} tests a	ш	-	-	-	-	-	-	-	-	-	-	-	-	-	=	=	=		-	-	
ondition	5	7	Q2					GND	GND					+125°C an	-55°C and	-	-	-	т	_	-	-	т	_	-	=	-	-	-	т	L	=	=	-	-	
minal co	4	ى ک	°,							GND	GND			cept T _c =	cept T _c =	т	-	-	_	т	-	-	_	т	-	-	7	т	-	=	=	=	=	-	-	
Ter	3	4	CLR1	4.5 V	4.5 V					GND	GND	5.5 V	5.5 V	group 1, ex	group 1, ex	в	=	-	A	В	в	A	A	в	в	A	A	в	=	=		A	=	-	-	
	2	ю	B1	4.5 V	4.5 V					GND	GND	GND	5.5 V	as for subg	as for subg	A	в	A	-		в	в	A		-	-	=	=	=	=	В	В	A	в	в	= -55°C.
	1	5	A1	ပ	υ					GND	GND	5.5 V	ပ	and limits a	and limits a	A	A	в	-	-	-	=	=		A	A	в	-	-	=		A	-	-	в	°C and T _C
	Cases E, F	Case 2	Test no.	33 CKT A. B. D. E	33 CKT C	34 CKT A, B, D, E	34 CKT C	35 CKT A, B, D, E	35 CKT C	36 CKT A, B, D, E	36 CKT C	37	38	Same tests, terminal conditions, and limits as for subgroup 1, except T_c = +125°C and V_{IC} tests are omitted.	Same tests, terminal conditions, and limits as for subgroup 1, except $T_{C} = -t$	39	40	41	42	43	44	45	46	47	48	49	50	51	52	53	54	55	" 56 " A	57	58	$T_{c} = +125^{\circ}$
		STD-883 method -	1	3011	=	- 4	=		=	- 4	=	3005	3005	s, terminal (s, terminal (3014	-		-			-	=			-				-	-	-	-	-	-	bgroup 7 at
				los								lcc1	lccs	Same tests	Same tests		table	tests																	_	Repeat sut
		Subgroup Symbol		-	Γc = 25°C										3		Tc = 25°C																			8

TABLE III. <u>Group A inspection for device type 02</u> - Continued.

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See footnotes at end of this table.

		Unit		ns		-		-	-		-		-		-	-	-	=	-	-	=			-	=					-	-			-	-		- sm	2 =	-
		Limits	Max	75	75	00	20	20	85	85	20	20	60	60 75	=	-	-	-	-	-	-	160		-	=			-	=	n =	-			-	-	-	. 08	;=	-
		Γi	Min	5		-	-	-	-	-	-	-	-	- 00	-	-	-	= :	-	-	-	20		-	-			-	= 000	-	-			-	-	-	57	;=	-
		Measured terminal		A1 to Q1	A2 to Q2	BZ 10 UZ	CLR1 to 01	CLR2 to 02	A2 to G2	A1 to G1	B1 to 01	B2 to 02	CLR2 to Q2	CLR1 to Q1 Q1	9' B	a'	a1	Q2	02 02	_ Q2	Q2	Q2	ā2	_ Q2	Q2	a1	ā1	'n	<u>8</u>	Ξıč		a1	6 6	2 i Č	4 1	02 02	200	02 02	ā2
	16	20	V _{cc}	5.0 V				-		-	-	-	-		-	-	-	-	-	-	-			-	-			-		-	-			-	-		. =	-	-
	15	19	Rext1	ш		ц	- z			ш	ш			z×	=	-	=									ڻ ا		-			-						T		
	14		Cext1	Ŀ		L	- z			ш	ш			N	-	-	-									сŋ -		-			-						T		
	13		а С	OUT		ШC	5										OUT									OUT				5			OUT						-
·/ /,				0		C		ц	ц			ц		oc			0		£	л			т	л		0							0	Ц	Ц		+	ц	ц
/ MOI (15	2 Q2		> `	>		OUT	V OUT			v out							OUT	OUT		Ċ	OUT	OUT										OUT	OUT	5	+	OUT	OUT
> ^ / >	11	14	CLR2		5.0 V	0.0		Z	5.0 V			5.0 V	Z					5.0 V	-	-	=			-	-								501	+	-	-	-	-	-
	10	13	B2		5.0 V	≧		≧	5.0 V			≧	Z					5.0 V	5.0 V	Z	=			5.0 V	5.0 V								50.1	5.0 V	Z	: -		-	5.0 V
a IIIay I	6	12	A2		z	GND		GND	Z			GND	GND					z	Z	GND	=		-	Z	Z								2	z	GND	;	. =	-	Z
olyl later	ø	10	GND	GND		-	-	-	-	-	-	-	=		-	-	-	-	-	-	=		-	-	=		-	-		-	-			-	-	-	: =	-	-
Terminal conditions (pins not designated may be migh ≥ 2.0 V,	7	6	Rext2		цι	L		z	ш			ш	z					¥	-	-	=	Ċ)		-	-								-	-	-	-	. –	> =	-
	9	8	Cext2		цι	L		z	ш			Ŀ	z					OPEN	-	-	=	G,		-	=								-		-		. –	>=	-
	5	7	Q2										OUT					OUT			OUT	OUT			OUT								Ξ	8		Ē		3	
	4	S	۱ġ				OUT			OUT	OUT				OUT	OUT											OUT	OUT		OUT	OUT	-			Ī		T		
	e	4	CLR1	5.0 V		2/	è.			5.0 V	5.0 V			N												5.0 V					-						T		
	2			5.0 V			zz			`	Z			N N N	_	z	z									5.0 V	V 0.9	Z			5.0 V		5.0 V				T		
-	1	2	A1	NI N			GND				GND			end R		GND	GND									z		GND			Z		z				1		-
-	Cases E, F		<u>.</u>		60			64	65	66	67 6	68		20		73 0		75	9	77	78	<u>م</u>	0	81		83			86	. 00	89	2	90	8	93	, ,	94 95	9	97
•						0 4	99	9	9	9	9	9	9		2	7	2	7	~	2	2	~	80	80	8	8	80	80	∞ c	0 00	80)	໑໐	ົດ	0		ກ ຫ) 0	6
		ol STD-883 method -		3003	_	-		=	-	-	-	-	=		-	-	-	-	-	-	-		•	-	•		•	-		•	-			•	-		=	-	•
-		p Symbol		tPLH1		^T PLH2	t _{PLH3}		t _{PHL1}		t _{PHL2}		t _{PHL3}	+	÷							t _{P2}							•	ξ.							÷	<u>^</u>	
		Subgroup		6	Tc = 25°C																																		

TABLE III. Group A inspection for device type 02 - Continued.

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See notes at end of this table.

		Unit		ms	-	-		-		
		∍								
		Limits	Max	8.0	-	-				
		Ľ	Min	5.7	-	-	-			
		Measured terminal		Q2	۵1 م	ā1	°1 0	۵1 م		
	16	20	V _{cc}	5.0 V		-	-			
	15	19	Rext1		ſ	=	=		ns;	
	14	18	Cext1		ſ	=	=	-	5 to 105	
	13	17	ð		OUT			OUT	s; t _{PLH3} is i ms.	
	12	15	ā2						+125°C and limits are as follows: t _{PLH} is 5 to 113 ns, t _{PLH} is 5 to 90 ns; t _{PLH} is 5 to 105 ns; 20 to 91 ns; t _{P2} is 70 to 195 ns; t _{P2} is 600 to 850 ns; and t _{P4} is 5.5 to 8.5 ms.	
	11	14	CLR2	5.0 V					is; t _{PLH2} is and t _P is	
 	10	13	B2	5.0 V					5 to 113 n o 850 ns:	
2	თ	12	A2	Z					t _{PLH1} is { is 600 t	
5	ω	10	GND	GND		=	=		follows: 95 ns: t _{ea}	
5	7	6	Rext2	h					ts are as s 70 to 19	
	9	8	Cext2	ſ					and limi	2°C
	ى ک	2	Q2	OUT					= +125°C s 20 to 9′	t T _c = -55°C
5	4	5	ō1			OUT	OUT		cept T _c :) ns: t _{er} is	0, excep
	ო	4	CLR1		5.0 V	-	-		oup 9, e) is 5 to 9(bgroup 1
	5	ĉ	B1		5.0 V	5.0 V	N	Z	as subgr ns: teur₃	as for su
	-	2	A1		N	Z	GND	GND	5 to 105	Inditions
	Cases E, F	Case 2	Test no.	98	66	100	101	102	S: tehio is	srminal cc
	-MIL-	Subgroup Symbol STD-883 method -		3003	Fig. 4	-	-		Same tests and terminal conditions as subgroup 9, except $T_{c} = +125$ °C and limits are as follows: t_{cLH} is 5 to 113 ns; t_{cLH} is 5 to 90 ns; t_{cLH} is 5 to 128 ns; t_{cLH} is 5 to 105 ns; t_{cH} is 5 to 90 ns; t_{cH} is 7 to 195 ns; t_{cH} is 600 to 850 ns; and t_{cc} is 5.5 to 8.5 ms.	11 Same tests and terminal conditions as for subgroup 10, except
		Symbol		t _{P5}					Same tu terri i is	Same te
		Subgroup {		ი	Tc = 25°C				10	1
		~		L	É				I	1

TABLE III. Group A inspection for device type 02 - Continued. Terminal conditions (pins not designated may be high ≥ 2.0 V, low ≤ 0.7 V, or open).

NOTES:

A. $V_{IN} = 3.0 V$ minimum.

B. $V_{IN} = 0.0 V$ or GND.

C. Apply input pulse

D. Test numbers 39 through 58 shall be run in sequence.

E. Output voltages shall be either:

H > 1.5 V; L < 1.5 V

Rext = 1.4 kΩ minimum to 70 kΩ maximum, connected to V_{cc} ; Cext ≤ 1,000 µF, connected to Rext terminal. ц.

G. Rext = 2 k\Omega ±10%, connected to V_{cc}; Cext = 80 pF ±10%, connected to Rext terminal.

1. Rext = 10 kΩ ±10%, connect to V_{cc} ; Cext = 100 pF ±10%, connected to Rext terminal.

J. Rext = 10 k\Omega $\pm 10\%$, connect to V_{cc}; Cext = 1.0 µF $\pm 10\%$, connected to Rext terminal.

K. Rext = 2 k $\Omega \pm 10\%$, connect to V_{cc}.

L. Note F may apply during subgroups 1, 2, and 3 testing if desired.

M. During subgroups 9, 10, 11 testing, Rext and Cext may remain applied on the side of the device not under test if desired.

N. Rext = 10 kΩ \pm 10%, connect to V_{cc}; Cext ≥ 45 pF connected to Rext terminal.

		Unit		>	=	=	=	=	=	=		-	HH	-	=	=	=			-	=	=		=	=	мА	=	=		-	=	=				В						
		ts	Max			0.4	0.4	-1.5	=	=	= :	- 00	-400	=	=	=	20	= :		= :	=	100		=	=	-100	007	- 130	-100	-130	11	11				See notes A, B						
		Limits	Min	2.5	2.5							001	- 100	-	=	=									T	-15	ç	00.1	-15	-30						See						
		Measured terminal		ø	١Ø	ø	١Ø	A1	A2	B1	B2	CLR	A1 A2	B1	B2	CLR	A1	A2	81	B2	CLR	A1	A2	- c	20	ξa	c	3	Ø	١Ø	Vcc	Vcc			AII	outputs	. =	-	= ;			
	14	20 t	Vcc	4.5 V	=	-	=	-	=	=	= :		> 0.0	-	-	=	=			= :	=	-		-	=	=	=	=		-	-	=			5.0 V	-	=	=	= ·		= :	
	13		Rext Cext (see I)				GND						0													GND									K 5	-	=	=	= '			=
	12	18	s ol	U			0											+							T	0										-				+	+	
· open).	~	~																																		<u> </u>	_				_	
.7 V, or	11	16	Cext (see I)																																¥	=	=	=				-
, low ≤ 0	10	4	S																																							
≥ 2.0 V	6	13	Rint	GND	4.5 V	4.5 V	GND																			GND		AND PIND	4.5 V	4.5 V	5.5 V	5.5 V										
Terminal conditions (pins not designated may be high ≥ 2.0 V, low ≤ 0.7 V, or open)	8	12	α	4 mA		4 mA																				GND		פואם							L	-	-	н	:	I.		_
ed may	7	10	GND	GND	=	=	-	=	=	=			=	=	=	=	=		= :	-	=	=		=	=	-	-	=		=	=	=	e omitted	e omitted	GND	-	=	=	= :		= :	=
lesignat	9	ი	ı۵		4 mA		4 mA																						GND	GND			c tests ar	tests are	т	-	=	_	I.	:	I	т
ns not c	5	ω	CLR	2.0 V	-	=	=				·	-18 mA		ľ		0.4 V					2.7 V				5 L L	4.5 V	-			=	5.5 V	5.5 V	C and V _L	and V _{IC}	В	В	A	A	ш	۲	B	A
tions (pi	4	9	B2 (0.7 V	0.7 V	۔ ۲				l8 mA	-		4.5 V	0.4 V	0		!	GND	_			4	GND	+	ں م	-		GND	GND	GND 5	_	c = 125°($c = -55^{\circ}C$	В	В	A	-	=		= ;	=
al condit	е К	4	B1	2.0 V	.0		2.0 V			-18 mA	-1	+		_	4.5 V 0.			_	2.7 V G	_			_		_	4.5 V	1 5 11	+	9	G	GND G	5.5 V 5.	except T	except T	~	В	_	-		= (B	
Termin				2.(-		2.(nA	-18		>	>>	-	4.5		Δ	_	2.1	ΰ	_	D	_	0	5	4.5		4			-		group 1,	group 1,			_			_	_	
	5	e	A2	/			,	A	-18 mA				V 4.0 V				GND	_	_			GND			-	_					/ 5.5 V		s as sub	ts as sub	В	A	A	В			A	-
	~	7	A1	0.7 V			0.7 V	-18 mA					0.4 V 4.5 V				2.7 V	GNE				5.5 V	GNE			GND				()	5.5 V	۔ ۱	and limit	and limit	В	A	A	В			-	=
	Case A,B,C,D	Case 2	Test no.	1	2	3	4	5	9	7	8	6	0 €	12	13	14	15	16	21	18	19	20	21	77	27	25 CKT	A,D		Z6 CKI A,D	26 CKT C	27	28	conditions,	conditions,	29	29A	30	31	321	33	34	35
	MIL-STD-	883 method		3006	3006	3007	3007					0000		-	-	=	3010	= :			=	-		-	-	3011	-	=		-	3005	3005	Same tests, terminal conditions, and limits as subgroup 1, except T_c = 125°C and V _{1C} tests are omitted	s, terminal c	Truth 3014 29 B B B B B B B B H GND	-	=	-	= :			=
		Symbol		V _{OH}		VoL		Vic				-	IL1 See	note C			I _{IH1}					I _{H2}				los					lcc1	lcc2	Same test	Same test	Truth	table	test					
		Subgroup		-	Tc = 25°C	1		I				1																			1	1	2			$Tc = 25^{\circ}C$						

TABLE III. Group A inspection for device type 03.

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See footnotes at end of this table.

		Unit			~										su	-	=	=	-	-	=	srí				
		_	Max		See notes A, B										50	61	32	8	49	50	205	6.0			ŗ	
		Limits	Min	-	See no										5 5	9	e	З	4	2J	5(3.5 6				
		be al	Σ		6	1	1	i	i		1				١Ŏ	ıα.	ø	ζ	a	١Ø		3.			ŗ	
		Measured terminal		AII	outputs	=	=	=	=		=	=	=		A1 to 0	B1 to ${\rm \bar Q}$	CLR to Q	A1 to Q	B1 to Q	CLR to	Ø	Ø	ls;			
	14	20	V _{cc}	5.0 V	=	-	-	-	=		=	-	=		5.0 V	=	-		-	=	-	-	5 to 57 r			
	13	19	<u>Rext</u> Cext (see I)	×	-	-	-	-	-	=	-	-	-		¥	×	Σ	х	×	Δ	ი	z	; t _{PLH1} is		1	
.(ui	12	18	NC																				5 to 48 ns			
TABLE III. Group A inspection for device type 03 – Continued. Terminal conditions (pins not designated may be high ≥ 2.0 V, low ≤ 0.7 V, or open).	11	16	Cext (see I)	×	=	-	=	-	-	-	-	-	-		×	×	Μ	Х	¥	Σ		ш	-125° C and limits are as follows: t_{PHL_1} is 50 to 75 ns; t_{PHL_2} is 5 to 92 ns; t_{PHL_3} is 5 to 48 ns; t_{PLH_1} is 5 to 57 ns;			
ontinued w ≤ 0.7 ^v	10	14	D NC																				5 to 92 n			
<u>e 03</u> – Co 2.0 V, lo	6	13	Rint																				IS; t _{PHL2} iS			
TABLE III. Group A inspection for device type $03 - Continued$. onditions (pins not designated may be high $\ge 2.0 \text{ V}$, low $\le 0.7 \text{ V}$	œ	12	a	т	_	_	т	_	_	Т	_	_	I				OUT	OUT	OUT		OUT	OUT	50 to 75 r			
on for de d may b	7	10	GND	GND	=	=	=	-	-	=	-	=	-		GND	=	=		-	=	=	-	:: t _{PHL1} is			
<u>nspectic</u> signated	9	6	١٥		н	Т		г	Т	L L	Т	Т	L L		OUT (OUT				OUT			s follows			
oup A ii not de			۲															V	>		>		its are a			
III. <u>Gr</u> Is (pins	5	8	CLR	A	В	A	A	В	A	A	B	A	A		5.0 V	5.0 V	Z		5.0 V	Z	5.0 V		and lim	.25 μs.	ŗ	
FABLE pndition	4	9	B2	A	ш	ш	A	=	-	=	=	=	=		5.0 V	5.0 V	Z	5.0 V	5.0 V	Z	5.0 V	5.0 V		3.0 to 6	= -55°C.	
- minal co	ю	4	B1	A	=	=	=	=	=	=	-	=	=		5.0 V	Z	5.0 V	5.0 V	Z	5.0 V	5.0 V	Z	cept T _c =	and t _{P4} is	cept T _C	
Ter	2	3	A2	A	=	=	=	=	-		-	=	В	= -55° C.	5.0 V	GND	GND	5.0 V	GND	GND	5.0 V	GND	oup 9 exc	: 308 ns; a	oup 10 ex	
	٢	2	A1	в	=	=	=	A	A	В	A	=	=	C and T _C =	Z	GND	GND	N	GND	GND	Z	GND	s as subgr	s; t _{P(MIN)} is	s as subgr	
	Case A,B,C,D	Case 2	Test no.	36	37	38	39	40	41	42	43	44	45	_c = +125° (46	47	48	49	50	51	52	53	al conditions	is 5 to 75 n	al conditions	
	MIL-STD-	883 method		3014	=	=	=	=	=	-	=	=	-	Repeat subgroup 7 at T_{c} = +125° C and T_{c} = -55° C.	3003	(Fig. 3)	-	-	-	-	=	-	Same tests and terminal conditions as subgroup 9 except $T_{\rm C}$ = -	t_{PLH2} is 5 to 74 ns; t_{PLH3} is 5 to 75 ns; $t_{P(MIN)}$ is 308 ns; and t_{P4} is 3.0 to 6.25 μ s.	Same tests and terminal conditions as subgroup 10 except $T_{\rm C}$ = -55 $^\circ\mathrm{C}.$	
		Symbol		Truth		test								Repeat sut	t _{PHL1}	t _{PHL2}	t _{PHL3}	t _{PLH1}	t _{PLH2}	t _{PLH3}	t _{P(MIN)}	t_{P4}	Same tests	t _{PLH2} is 5 to	Same tests	ΞS:
		Subgroup		7	$Tc = 25^{\circ}C$									∞	-	Tc = 25°C							10		11	NOTES:

A. $V_{IN} = 3.0 V$ minimum. B. $V_{IN} = 0.0 V$ or GND. C. For circuit D, IIL1 limits are 120 to 360 mA. D. Test numbers 29 through 45 shall be run in sequence. E. Output voltages shall be either.

H > 1.5 V; L < 1.5 V Cext connected to Rext/Cext through a 1,000 pF $\pm 10\%$ capacitor.

Rext/Cext connected to Vcc through a 5 kΩ $\pm10\%$ resistor. Note K may apply during subgroups 1, 2, and 3 testing if desired. ட் ப் _- --

Apply input pulse

- - 2.5 V min/5.5 V max.
 0 V

Rext/Cext connected to V_{cc} through a 5 kΩ to 180 kΩ resistor, and Cext connected to Rext/Cext through a ≤ 1,000 µF capacitor.

Cext connected to Rext/Cext through A \ge 45 pF capacitor, Rext/Cext connected to V_{cc} through a 10 kΩ \pm 10% resistor. Rext/Cext connected to V_{cc} through a 10 kΩ \pm 10% resistor. żΞż

5. PACKAGING

5.1 <u>Packaging requirements.</u> For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When actual packaging of materiel is to be performed by DoD personnel, these personnel need to contact the responsible packaging activity to ascertain requisite packaging requirements. Packaging requirements are maintained by the Inventory Control Point's packaging activity within the Military Department of Defense Agency, or within the Military Department's System Command. Packaging data retrieval is available from the managing Military Department's or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

6. NOTES

(This section contains information of a general or explanatory nature which may be helpful, but is not mandatory.)

6.1 <u>Intended use.</u> Microcircuits conforming to this specification are intended for original equipment design applications and logistic support of existing equipment.

- 6.2 Acquisition requirements. Acquisition documents should specify the following:
 - a. Title, number, and date of the specification.
 - b. Complete part number (see 1.2).
 - c. Requirements for delivery of one copy of the quality conformance inspection data pertinent to the device inspection lot to be supplied with each shipment by the device manufacturer, if applicable.
 - d. Requirements for certificate of compliance, if applicable.
 - e. Requirements for notification of change of product or process to contracting activity in addition to notification to the qualifying activity, if applicable.
 - f. Requirements for failure analysis (including required test condition of method 5003 of MIL-STD-883), corrective action, and reporting of results, if applicable.
 - g. Requirements for product assurance options.
 - h. Requirements for special carriers, lead lengths, or lead forming, if applicable. These requirements should not affect the part number. Unless otherwise specified, these requirements will not apply to direct purchase by or direct shipment to the Government.
 - j. Requirements for "JAN" marking.

6.3 <u>Superseding information</u>. The requirements of MIL-M-38510 have been superseded to take advantage of the available Qualified Manufacturer Listing (QML) system provided by MIL-PRF-38535. Previous references to MIL-M-38510 in this document have been replaced by appropriate references to MIL-PRF-38535. All technical requirements now consist of this specification and MIL-PRF-38535. The MIL-M-38510 specification sheet number and PIN have been retained to avoid adversely impacting existing government logistics systems and contractor's parts lists.

6.4 <u>Qualification</u>. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturers List QML-38535 whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or purchase orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from DSCC-VQ, 3990 E. Broad Street, Columbus, Ohio 43123-1199.

6.5 <u>Abbreviations, symbols, and definitions.</u> The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535, MIL-HDBK-1331, and as follows:

GND	Ground zero voltage potential
l _{in}	Current flowing into an input terminal
V _{IC}	Input clamp voltage
V _{IN}	Voltage level at an input terminal

6.6 <u>Logistic support.</u> Lead materials and finishes (see 3.4) are interchangeable. Unless otherwise specified, microcircuits acquired for Government logistic support will be acquired to device class B (see 1.2.2), lead material and finish A (see 3.4). Longer length leads and lead forming should not affect the part number.

6.7 <u>Substitutability.</u> The cross-reference information below is presented for the convenience of users. Microcircuits covered by this specification will functionally replace the listed generic-industry type. Generic-industry microcircuit types may not have equivalent operational performance characteristics across military temperature ranges or reliability factors equivalent to MIL-M-38510 device types and may have slight physical variations in relation to case size. The presence of this information should not be deemed as permitting substitution of generic-industry types for MIL-M-38510 types or as a waiver of any of the provisions of MIL-PRF-38535.

Military device	Generic-industry
type	type
01	54LS123, 74LS123
02	54LS221, 74LS221
03	54LS122, 74LS122

6.8 <u>Manufacturers' designation</u>. Manufacturers' circuits, which form a part of this specification, are designated as shown in table IV herein.

		M	anufacturers		
	А	В	С	D	E
Device	Texas Instru-	Signetics	National	Motorola	Raytheon
type	ments Inc.	Corporation	Semiconductor Corp	Inc	Company
01	Х		Х	Х	
02	X	x	Х	X	
03	Х		Х	Х	Х

TABLE IV. Manufacturers' designation.

6.9 <u>Changes from previous issue.</u> Asterisks are not used in this revision to identify changes with respect to the previous issue due to the extensiveness of the changes.

Custodians: Army - CR Navy - EC Air Force - 11 DLA - CC

Review activities: Army - MI, SM Navy - AS, CG, MC, SH, TD Air Force - 03, 19, 99 Preparing activity: DLA - CC

(Project 5962-1964)

STANDARDIZ	ATION DOCUMENT IMPROV	EMENT PROPOSAL
1. The preparing activity must complete block	INSTRUCTIONS is 1, 2, 3, and 8. In block 1, both the docu	ment number and revision letter should be given.
2. The submitter of this form must complete b	locks 4, 5, 6, and 7, and send to preparing	g activity.
3. The preparing activity must provide a reply	within 30 days from receipt of the form.	
		vers, or clarification of requirements on current contracts. portion of the referenced document(s) or to amend
I RECOMMEND A CHANGE:	1. DOCUMENT NUMBER MIL-M-38510/314C	2. DOCUMENT DATE (YYYYMMDD) 2003-07-14
3. DOCUMENT TITLE MICROCIRCUITS, DIGITAL, LOW-PO	WER SCHOTTKY TTL, MONOSTAB	LE MULTIVIBRATORS, MONOLITHIC SILICON
4. NATURE OF CHANGE (Identify paragraph i	number and include proposed rewrite, if po	ossible. Attach extra sheets as needed.)
5. REASON FOR RECOMMENDATION		
6. SUBMITTER		
a. NAME (Last, First Middle Initial)	b. ORGANIZATION	1
c. ADDRESS (Include Zip Code)	d. TELEPHONE (<i>Ir</i> (1) Commercial (2) DSN (<i>If applicable</i>)	aclude Area Code) 7. DATE SUBMITTED (YYYYMMDD)
8. PREPARING ACTIVITY		
a. NAME Defense Supply Center, Columbus	b. TELEPHONE <i>(Ir</i> (1) Commercial 6	
c. ADDRESS (Include Zip Code) DSCC-VA P. O. Box 3990 Columbus, Ohio 43216-5000	Defense Standar 8725 John J. Kin Fort Belvoir, Virgi	ECEIVE A REPLY WITHIN 45 DAYS, CONTACT: dization Program Office (DLSC-LM) gman Road, Suite 2533 nia 22060-6221 767-6888 DSN 427-6888
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